

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of manufacturing a semiconductor device, comprising the step of selectively grinding or polishing the peripheral portion and the beveled portion of a target substrate including a semiconductor substrate.

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The grinding or polishing of the target substrate is performed after the dry etching step for forming a trench in the target substrate, or after the

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depositing step of a copper layer providing a source of contamination of the process apparatus in forming a Cu-buried wiring. By grinding or polishing the peripheral portion and the beveled portion of the target substrate, the uneven portion in the peripheral portion and the beveled portion can be removed and

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copper is prevented from being exposed to the outside, thereby avoiding the particle generation and contamination of the process apparatus.

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